

Abstract

Method for masking a recess in a structure having a high aspect ratio

A method for selective masking is described. In this case, a filling material is applied to a structure which, as a function of the aspect ratio of the structure, forms cavities when the aspect ratio is high. The filling layer is then removed as far as the cavities and, using an etching process, filling material is removed completely from the recesses in which the cavities are formed. In this way, areas are exposed selectively.

Figure 4

List of reference symbols

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|----|-----------------------|
| 1 | 1st recess |
| 2 | 2nd recess |
| 3 | Silicon wafer |
| 4 | Web |
| 5 | Filling layer |
| 6 | Cavities |
| 7 | Liquid gas source |
| 8 | Heat source |
| 9 | Valve |
| 10 | Vacuum pumping system |
| 11 | Three-zone oven |
| 12 | Sacrificial layer |